

# Olivier Marcelot

## List of Publications by Year in descending order

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22  
papers

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citations

1040056

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h-index

839539

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g-index

22  
all docs

22  
docs citations

22  
times ranked

230  
citing authors

#	ARTICLE	IF	CITATIONS
1	CMOS Pixel Potentials Extraction Method From Test Structures Based on EKV Model. IEEE Transactions on Electron Devices, 2021, 68, 2835-2840.	3.0	1
2	Modeling, Simulation Methods and Characterization of Photon Detection Probability in CMOS-SPAD. Sensors, 2021, 21, 5860.	3.8	10
3	Mitigation of Parasitic Light Sensitivity in Global Shutter CMOS Image Sensors Through Use of Correction Frame. IEEE Transactions on Electron Devices, 2021, 68, 4491-4496.	3.0	2
4	Extraction of acceptor concentration map from EBIC experiments. Ultramicroscopy, 2021, 228, 113339.	1.9	0
5	Capacitive Trench-Based Charge Transfer Device. IEEE Electron Device Letters, 2020, 41, 1388-1391.	3.9	8
6	Phosphorus Versus Arsenic: Role of the Photodiode Doping Element in CMOS Image Sensor Radiation-Induced Dark Current and Random Telegraph Signal. IEEE Transactions on Nuclear Science, 2020, 67, 1241-1250.	2.0	4
7	Dark Count Rate Modeling in Single-Photon Avalanche Diodes. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 1507-1515.	5.4	17
8	High Displacement Damage Dose Effects in Radiation Hardened CMOS Image Sensors. IEEE Transactions on Nuclear Science, 2020, 67, 1256-1262.	2.0	3
9	Exploration of Pinned Photodiode Radiation Hardening Solutions Through TCAD Simulations. IEEE Transactions on Electron Devices, 2019, 66, 3411-3416.	3.0	9
10	A Fast Method for Modeling and Optimizing Parasitic Light Sensitivity in Global Shutter CMOS Image Sensors. , 2019, , .		1
11	Leakage Current Non-Uniformity and Random Telegraph Signals in CMOS Image Sensor Floating Diffusions Used for In-Pixel Charge Storage. Sensors, 2019, 19, 5550.	3.8	7
12	From EBIC images to qualitative minority carrier diffusion length maps. Ultramicroscopy, 2019, 197, 23-27.	1.9	6
13	Influence of Pixel Design on Charge Transfer Performances in CMOS Image Sensors. IEEE Transactions on Electron Devices, 2018, 65, 1048-1055.	3.0	19
14	Total Ionizing Dose Effects on a Radiation-Hardened CMOS Image Sensor Demonstrator for ITER Remote Handling. IEEE Transactions on Nuclear Science, 2018, 65, 101-110.	2.0	26
15	Pinned Photodiode CMOS Image Sensor TCAD Simulation: In-Depth Analysis of in-Pixel Pinning Voltage Measurement for a Diagnostic Tool. IEEE Transactions on Electron Devices, 2017, 64, 455-462.	3.0	19
16	Radiation Hardening of Digital Color CMOS Camera-on-a-Chip Building Blocks for Multi-MGy Total Ionizing Dose Environments. IEEE Transactions on Nuclear Science, 2017, 64, 45-53.	2.0	26
17	Dark Current Sharing and Cancellation Mechanisms in CMOS Image Sensors Analyzed by TCAD Simulations. IEEE Transactions on Electron Devices, 2017, 64, 4985-4991.	3.0	12
18	Enhanced Near-Infrared Response CMOS Image Sensors Using High-Resistivity Substrate: Photodiodes Design Impact on Performances. IEEE Transactions on Electron Devices, 2016, 63, 120-127.	3.0	9

#	ARTICLE	IF	CITATIONS
19	Pixel Level Characterization of Pinned Photodiode and Transfer Gate Physical Parameters in CMOS Image Sensors. IEEE Journal of the Electron Devices Society, 2014, 2, 65-76.	2.1	41
20	Plan View and Cross-Sectional View EBIC Measurements: Effect of e-Beam Injection Conditions on Extracted Minority Carrier Transport Properties. IEEE Transactions on Electron Devices, 2014, 61, 2437-2442.	3.0	6
21	Comparison between TCAD simulated and measured carrier lifetimes in CMOS photodiodes using the Open Circuit Voltage Decay method. Solid-State Electronics, 2013, 81, 135-139.	1.4	1
22	Radiation Effects in Pinned Photodiode CMOS Image Sensors: Pixel Performance Degradation Due to Total Ionizing Dose. IEEE Transactions on Nuclear Science, 2012, 59, 2878-2887.	2.0	78